

SCR

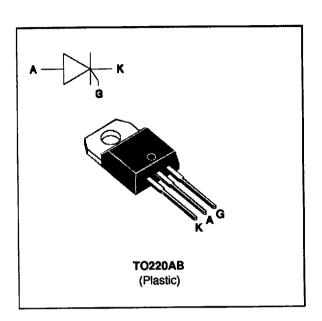
FEATURES

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY

DESCRIPTION

The TYN 225 ---> TYN 1025 Family Silicon Controlled Rectifiers are high performance glass passivated chips technology.

This general purpose Family Silicon Controlled Rectifiers is designed for power supply up to 400Hz on resistive or inductive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Parameter		
IT(RMS)	RMS on-state current (180° conduction angle)	Tc = 95 °C	25	A
lT(AV)	Average on-state current (180° conduction angle, single phase circuit)	Tc = 95 °C	16	A
ITSM	Non repetitive surge peak on-state current	tp = 8.3 ms 260	260	A
	(Tj initial = 25°C)	tp = 10 ms	250	
I2t	I2t value	tp = 10 ms	310	A ² s
di/dt	Critical rate of rise of on-state current Gate supply: IG = 100 mA diG/dt = 1 A/µs		100	A/µs
Tstg Tj	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	. €
TI	Maximum lead temperature for soldering during 10 from case	sat 4.5 mm	260	•C

Symbol	Parameter		TYN				Unit	
		225	425	625	825	1025	1225	
V _{DRM} VRRM	Repetitive peak off-state voltage Tj = 125 °C	200	400	600	800	1000	1200	٧

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TYN 225 ---> TYN 1225

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	60	•C/W
Rth (j-c) DC	Junction to case for DC	1.3	•C/W

GATE CHARACTERISTICS (maximum values)

 P_{G} (AV) = 1W P_{GM} = 10W (tp = 20 μ s) I_{FGM} = 4A (tp = 20 μ s) V_{RGM} = 5 V.

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
lgt	V _D =12V (DC) R _L =33Ω	Tj=25°C	MAX	40	mA
VGT	V _D =12V (DC) R _L =33Ω	Tj=25°C	MAX	1.5	V
VGD	V _D =V _{DRM} R _L =3.3kΩ	Tj= 125°C	MIN	0.2	V
tgt	V _D =V _{DRM} I _G = 200mA dI _G /dt = 1.5A/μs	Tj=25°C	TYP	2	μs
١L	IG= 1.2 IGT	Tj=25°C	TYP	80	mA
lн	IT= 100mA gate open	Tj=25°C	MAX	50	mA
VTM	ITM= 50A tp= 380µs	Tj=25°C	MAX	1.6	V
IDRM	VDRM Rated	Tj=25°C	MAX	0.01	mA
IRRM	VRRM Rated	Tj= 125°C		4	
dV/dt	Linear slope up to VD=67%VDRM gate open	Tj= 125°C	MIN	500	V/µs
tq	V _D =67%V _{DRM} I _{TM} = 50A V _R = 25V dI _{TM} /dt=30 A/μs dV _D /dt= 50V/μs	Tj= 125°C	TYP	70	μѕ

Fig.1: Maximum average power dissipation versus average on-state current.

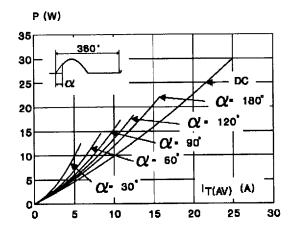


Fig.3: Average on-state current versus case temperature.

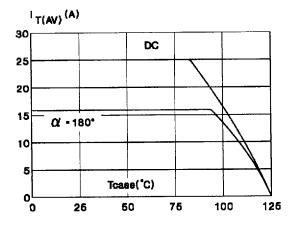


Fig.5: Relative variation of gate trigger current versus junction temperature.

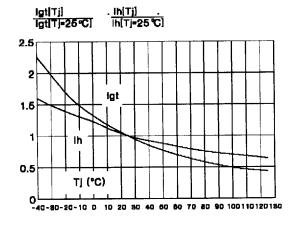


Fig.2: Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

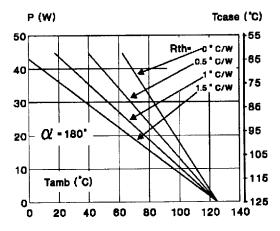


Fig.4: Relative variation of thermal impedance versus pulse duration.

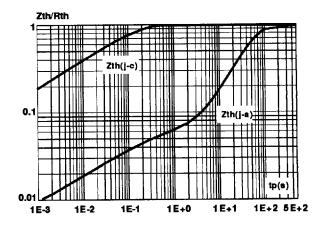


Fig.6: Non repetitive surge peak on-state current versus number of cycles.

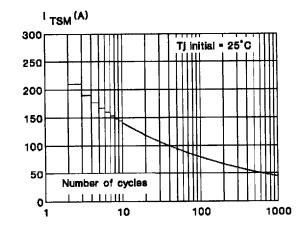
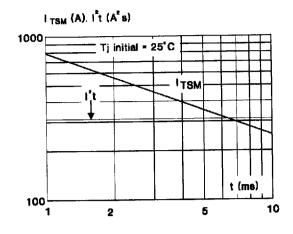
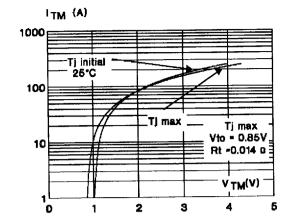


Fig.7: Non repetitive surge peak on-state current for a sinusoidal pulse with width : t ≤ 10 ms, and corresponding value of I2t.

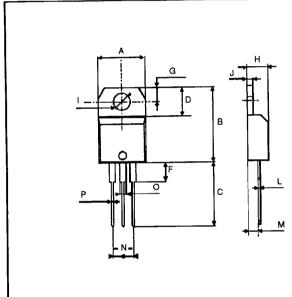
Fig.8: On-state characteristics (maximum values).





PACKAGE MECHANICAL DATA

TO220AB Plastic



REF.	DIMENSIONS				
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	10.00	10.40	0.393	0.409	
В	15.20	15.90	0.598	0.625	
С	13.00	14.00	0.511	0.551	
D	6.20	6.60	0.244	0.259	
F	3.50	4.20	0.137	0.165	
G	2.65	2.95	0.104	0.116	
Н	4.40	4.60	0.173	0.181	
	3.75	3.85	0.147	0.151	
J	1.23	1.32	0.048	0.051	
L	0.49	0.70	0.019	0.027	
М	2.40	2.72	0.094	0.107	
Z	4.80	5.40	0.188	0.212	
0	1.14	1.70	0.044	0.066	
Р	0.61	0.88	0.024	0.034	

Cooling method: C Marking: type number Recommended torque value: 0.8 m.N. Maximum torque value : 1 m.N.

Weight: 2.3 g

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